

RGS80TSX2HR

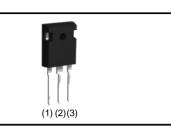
1200V 40A Field Stop Trench IGBT

Gate Collector

Emitter

V _{CES}	1200V
Ι _{C (100°C)}	40A
V _{CE(sat) (Typ.)}	1.7V
P _D	555W

•Outline TO-247N



●Inner Circuit

Features

- 1) Low Collector Emitter Saturation Voltage
- 2) Short Circuit Withstand Time 10µs
- 3) Qualified to AEC-Q101
- 4) Pb free Lead Plating ; RoHS Compliant

Application

Heater for Automotive

	(1) (2) (3)
--	-------------------

Packaging Specifications

Туре	Packaging	Tube
	Reel Size (mm)	-
	Tape Width (mm)	-
	Basic Ordering Unit (pcs)	450
	Packing Code	C11
	Marking	RGS80TSX2

●Absolute Maximum Ratings (at T_C = 25°C unless otherwise specified)

Parameter		Symbol	Value	Unit
Collector - Emitter Voltage		V _{CES}	1200	V
Gate - Emitter Voltage		V _{GES}	±30	V
Collector Current	$T_{\rm C} = 25^{\circ}{\rm C}$	Ι _C	80	A
Collector Current	$T_{\rm C} = 100^{\circ}{\rm C}$	Ι _C	40	A
Pulsed Collector Current		I _{CP} *1	120	A
Power Dissipation	$T_{\rm C} = 25^{\circ}{\rm C}$	P _D	555	W
Power Dissipation	$T_{\rm C} = 100^{\circ}{\rm C}$	P _D	277	W
Operating Junction Temperature		T _j	-40 to +175	°C
Storage Temperature		T _{stg}	-55 to +175	°C

*1 Pulse width limited by T_{imax.}

•Thermal Resistance

Baramotor	Symbol	Values			Unit
Parameter	Symbol	Min.	Тур.	Max.	Unit
Thermal Resistance IGBT Junction - Case	$R_{\theta(j\text{-}c)}$	-	-	0.27	°C/W

●IGBT Electrical Characteristics (at T_j = 25°C unless otherwise specified)

Parameter	Symbol	Conditions	Values			Unit	
Farameter	Symbol	Conditions	Min.	Тур.	Max.	Onit	
Collector - Emitter Breakdown Voltage	BV _{CES}	$I_{\rm C}$ = 10µA, $V_{\rm GE}$ = 0V	1200	-	-	V	
		$V_{CE} = 1200V, V_{GE} = 0V,$					
Collector Cut - off Current	I _{CES}	T _j = 25°C Tj = 175°C ^{*2}	-	-	10	μA	
		Tj = 175°C ^{*2}	-	3	-	mA	
Gate - Emitter Leakage Current	I _{GES}	$V_{GE} = \pm 30 V$, $V_{CE} = 0 V$	-	-	±500	nA	
Gate - Emitter Threshold Voltage	$V_{GE(th)}$	V _{CE} = 5V, I _C = 6.1mA	5.0	6.0	7.0	V	
		I _C = 40A, V _{GE} = 15V,					
Collector - Emitter Saturation Voltage	V _{CE(sat)}	T _j = 25°C	-	1.70	2.10	V	
-		T _j = 175°C	-	2.20	-	V	

RGS80TSX2HR

•IGBT Electrical Characteristics (at	$_{i} = 25^{\circ}$ C unless otherwise specified)
--------------------------------------	---------------------------------------------------

	Symbol	Conditions	Values			
Parameter			Min.	Тур.	Max.	Unit
Input Capacitance	C _{ies}	V _{CE} = 30V,	-	2820	-	
Output Capacitance	C _{oes}	$V_{GE} = 0V,$	-	161	-	рF
Reverse transfer Capacitance	C _{res}	f = 1MHz	-	25	-	
Total Gate Charge	Qg	V _{CE} = 500V,	-	104	-	
Gate - Emitter Charge	Q _{ge}	I _C = 40A,	-	25	-	nC
Gate - Collector Charge	Q _{gc}	V _{GE} = 15V	-	42	-	
Turn - on Delay Time	t _{d(on)}		-	49	-	
Rise Time	t _r	I _C = 40A, V _{CC} = 600V, V _{GE} = 15V, R _G = 10Ω,	-	27	-	
Turn - off Delay Time	t _{d(off)}	$T_i = 25^{\circ}C$	-	199	-	ns
Fall Time	t _f	Inductive Load	-	227	-	
Turn - on Switching Loss	Eon	*E _{on} include diode reverse recovery	-	3.00	-	mJ
Turn - off Switching Loss	E _{off}		-	3.10	-	
Turn - on Delay Time	t _{d(on)}		-	49	-	
Rise Time	tr	I _C = 40A, V _{CC} = 600V, V _{GE} = 15V, R _G = 10Ω,	-	40	-	ns
Turn - off Delay Time	t _{d(off)}	$T_i = 175^{\circ}C$	-	258	-	
Fall Time	t _f	Inductive Load	-	371	-	
Turn - on Switching Loss	E_{on}	*E _{on} include diode reverse recovery	-	3.80	-	
Turn - off Switching Loss	E _{off}		-	4.50	-	mJ
Reverse Bias Safe Operating Area	RBSOA	$\begin{split} I_{C} &= 120 \text{A}, \ V_{CC} = 1050 \text{V}, \\ V_{P} &= 1200 \text{V}, \ V_{GE} = 15 \text{V}, \\ R_{G} &= 50 \Omega, \ T_{j} = 175^{\circ} \text{C} \end{split}$	FULL SQUARE		-	
Short Circuit Withstand Time	t _{sc}	V _{CC} ≤ 600V, V _{GE} = 15V, T _j = 25°C	10	-	-	μs
Short Circuit Withstand Time	t _{sc} *2	V _{CC} ≤ 600V, V _{GE} = 15V, T _j = 150°C	8	-	-	μs

*2 Design assurance without measurement

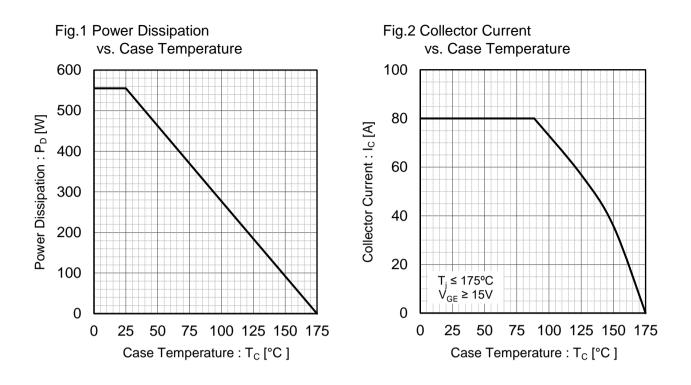
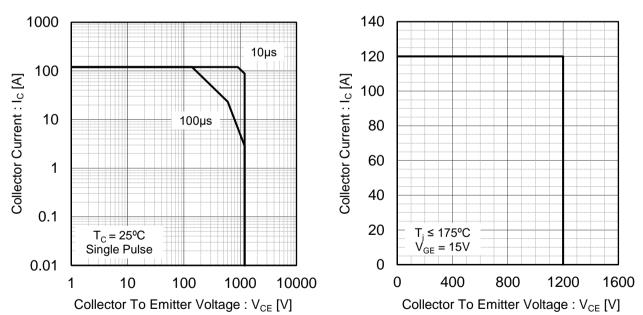
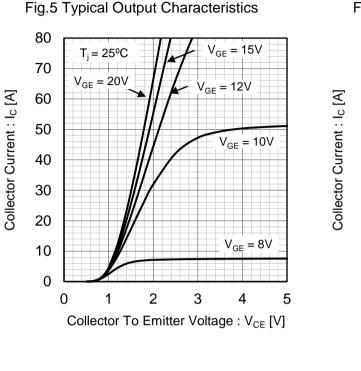


Fig.3 Forward Bias Safe Operating Area







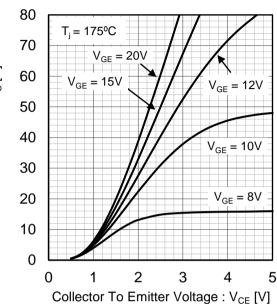
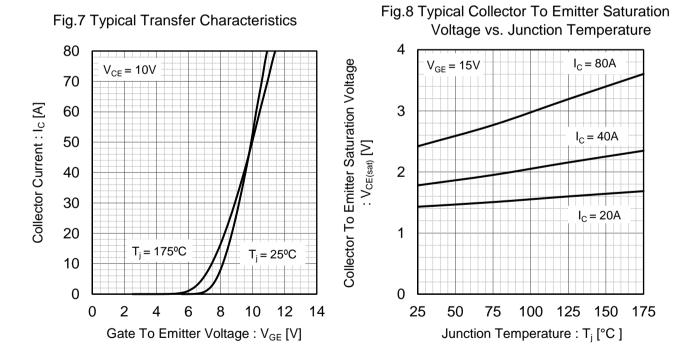
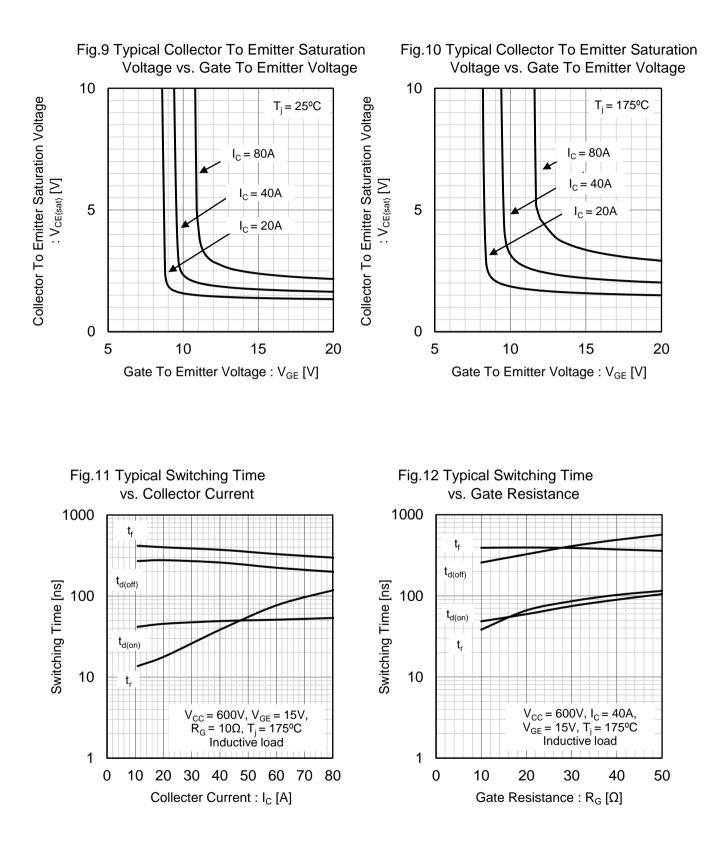


Fig.6 Typical Output Characteristics





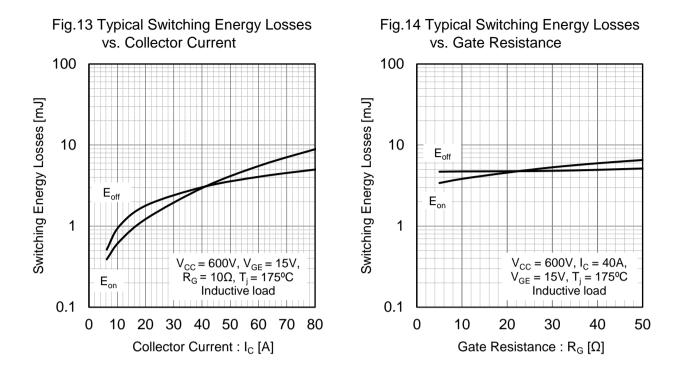
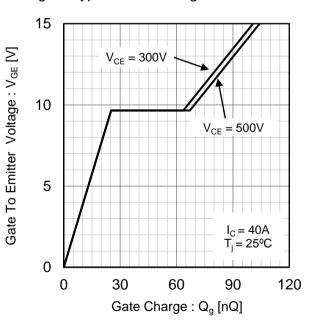


Fig.15 Typical Capacitance vs. Collector To Emitter Voltage 10000 Cies 1000 Capacitance [pF] C_{oes} 100 10 C_{res} f = 1MHz $V_{GE} = 0V$ T_i = 25⁰C 1 0.01 0.1 1 10 100 Collector To Emitter Voltage : V_{CE} [V]

Fig.16 Typical Gate Charge



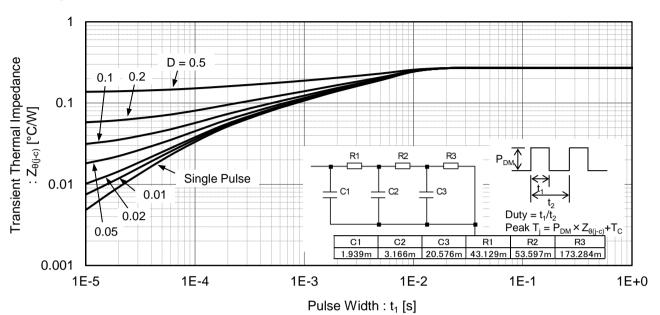


Fig.17 IGBT Transient Thermal Impedance

8/9



Inductive Load Switching Circuit and Waveform

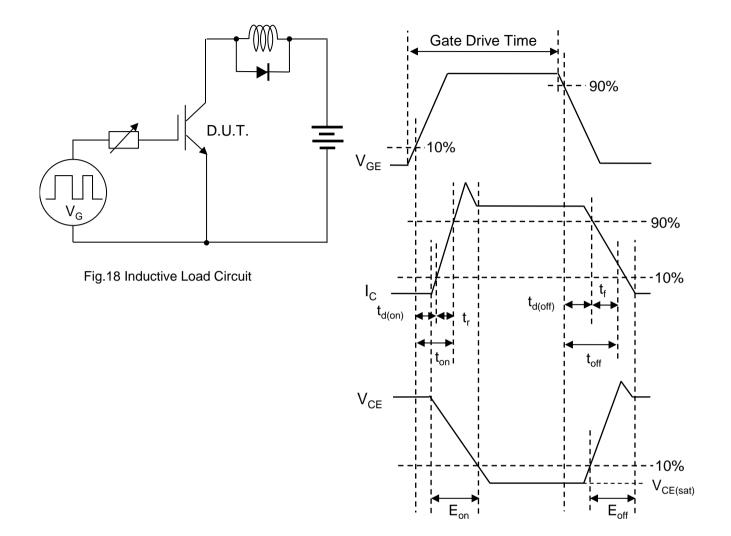


Fig.19 Inductive Load Waveform

9/9



	Notes
1)	The information contained herein is subject to change without notice.
2)	Before you use our Products, please contact our sales representative and verify the latest specifica- tions.
3)	Although ROHM is continuously working to improve product reliability and quality, semicon- ductors can break down and malfunction due to various factors. Therefore, in order to prevent personal injury or fire arising from failure, please take safety measures such as complying with the derating characteristics, implementing redundant and fire prevention designs, and utilizing backups and fail-safe procedures. ROHM shall have no responsibility for any damages arising out of the use of our Poducts beyond the rating specified by ROHM.
4)	Examples of application circuits, circuit constants and any other information contained herein are provided only to illustrate the standard usage and operations of the Products. The periphera conditions must be taken into account when designing circuits for mass production.
5)	The technical information specified herein is intended only to show the typical functions of and examples of application circuits for the Products. ROHM does not grant you, explicitly or implicitly any license to use or exercise intellectual property or other rights held by ROHM or any other parties. ROHM shall have no responsibility whatsoever for any dispute arising out of the use of such technical information.
6)	The Products specified in this document are not designed to be radiation tolerant.
7)	For use of our Products in applications requiring a high degree of reliability (as exemplified below), please contact and consult with a ROHM representative : transportation equipment (i.e cars, ships, trains), primary communication equipment, traffic lights, fire/crime prevention, safety equipment, medical systems, servers, solar cells, and power transmission systems.
8)	Do not use our Products in applications requiring extremely high reliability, such as aerospace equipment, nuclear power control systems, and submarine repeaters.
9)	ROHM shall have no responsibility for any damages or injury arising from non-compliance with the recommended usage conditions and specifications contained herein.
10)	ROHM has used reasonable care to ensure the accuracy of the information contained in this document. However, ROHM does not warrants that such information is error-free, and ROHM shall have no responsibility for any damages arising from any inaccuracy or misprint of such information.
11)	Please use the Products in accordance with any applicable environmental laws and regulations such as the RoHS Directive. For more details, including RoHS compatibility, please contact a ROHM sales office. ROHM shall have no responsibility for any damages or losses resulting non-compliance with any applicable laws or regulations.
12)	When providing our Products and technologies contained in this document to other countries you must abide by the procedures and provisions stipulated in all applicable export laws and regulations, including without limitation the US Export Administration Regulations and the Foreign Exchange and Foreign Trade Act.
13)	This document, in part or in whole, may not be reprinted or reproduced without prior consent or ROHM.



Thank you for your accessing to ROHM product informations. More detail product informations and catalogs are available, please contact us.

ROHM Customer Support System

http://www.rohm.com/contact/

Mouser Electronics

Authorized Distributor

Click to View Pricing, Inventory, Delivery & Lifecycle Information:

ROHM Semiconductor: RGS80TSX2HRC11